Growth of La₂Zr₂O₇, La₂Hf₂O₇ and Lu₃TaO₇ single crystals with high melting point by micro-pulling-down method and their optical properties

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Introduction

Iridium (Ir) and Platinum (Pt) crucibles have been generally used in the micro-pulling-down (μ -PD) method for crystal growth of functional oxide single crystals. However, the melting point (m.p.) of Ir is about 2450°C, and materials research of single crystals by the μ -PD method has basically been limited to materials with m.p. below 2200°C. While Rhenium (Re) crucible enables crystal growths of sesquioxide, it is not currently used due to the rarity of the element. On the other hand, Tungsten (W) and Molybdenum (Mo) with higher m.p. than Ir have been used for crystal growth of sapphire single crystals. W and Mo crucibles have not been used in a wide range of materials due to concerns about reaction with oxides. In this study, we tried to establish growth technique of oxide single crystals with over 2200°C using W and Mo crucibles, and material research in high temperature range were performed for La₂Zr₂O₇ (m.p.: 2283°C), La₂Hf₂O₇ (m.p.: 2418°C) and Lu₃TaO₇ (m.p.: 2380°C) single crystals.

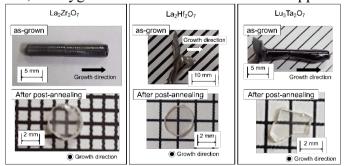
Experimental

ZrO₂, HfO₂, Ta₂O₅ (>3N), La₂O₃, CeO₂, Eu₂O₃, and Er₂O₃ (>4N), powders were mixed as nominal compositions of La₂Zr₂O₇, La₂Hf₂O₇ and Lu₃TaO₇, and mixed powders were sintered at 1600°C for 24 hours in air. In addition, sintered powders of specimens including dopant (Ce, Eu or Er) were also prepared. The sintered powder was set in W or Mo crucibles with a die at the bottom, and the crucible and deoxygenated ZrO₂ insulators were set in the center of a high-frequency induction coil. Deoxygenated ZrO₂ insulators were prepared by sintering the commercial ZrO₂ insulators at 2000°C in Ar using a carbon electrical furnace. The crucible was heated up to the m.p. of the target material, and single crystal was grown using a W rod as a seed. Phase identifications and crystallinity evaluations of obtained crystals were performed by measurements of powder X-ray diffraction (XRD), Laue camera, pole figure and X-ray rocking curve (XRC). Optical and scintillation properties of crystals with dopant were also evaluated.

Results and discussions

Crystal growth of La₂Zr₂O₇ single crystals were grown by the μ-PD method using Mo or W crucibles. While the Mo crucible deteriorated after crystal growth, W crucible could be used stable without the deterioration. In addition, deoxygenated ZrO₂ insulators could suppress

oxidation of W crucible, and La₂Zr₂O₇ single crystal could be obtained (Fig.1). La₂Hf₂O₇ and Lu₃TaO₇ single crystals were also able to be grown under the similar conditions.[1] After postannealing in air, grown crystals indicated high transparency. Eu or Er-doped La₂Zr₂O₇ and La₂Hf₂O₇ single crystals indicated emission light originating from dopants. Details of crystal growths and optical properties will be reported. **References**



dopants. Details of crystal growths and Fig. 1 As-grown La₂Zr₂O₇, La₂Hf₂O₇ and Lu₃TaO₇ optical properties will be reported.

References single crystals grown by μ-PD method using W crucible and polished specimens after post-annealing.

[1] T. Suda, Y. Yokota, et al., Crystal growth of La₂Hf₂O₇ by micro-pulling-down method using W crucible. J. Cryst. Growth. 2022;583:126547.